

Polar2™ HiperFET™ Power MOSFET

IXFH42N50P2 IXFT42N50P2

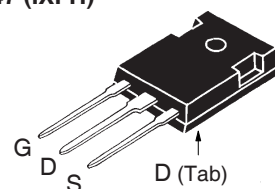
$$\begin{aligned} V_{DSS} &= 500V \\ I_{D25} &= 42A \\ R_{DS(on)} &\leq 145m\Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

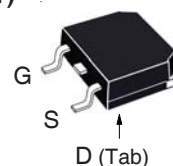


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	42	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	126	A
I_A	$T_C = 25^\circ\text{C}$	42	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.4	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	15	V/ns
P_D	$T_C = 25^\circ\text{C}$	830	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062in.) from Case for 10s	300	$^\circ\text{C}$
T_{sold}	Plastic Body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4mA$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			10 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			145 m Ω

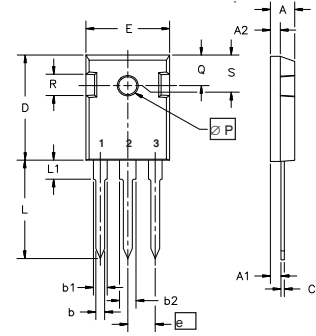
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}, \text{Note 1}$	23	36	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		5300	pF
C_{oss}			555	pF
C_{rss}			43	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External)		23	ns
t_r			12	ns
$t_{d(off)}$			42	ns
t_f			9	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		92	nC
Q_{gs}			26	nC
Q_{gd}			36	nC
R_{thJC}			0.21	0.15°C/W
R_{thCS}				$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			42 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			168 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}, \text{Note 1}$			1.3 V
t_{rr}	$I_F = 21\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 85\text{V}, V_{GS} = 0\text{V}$		12	250 ns
I_{RM}				A
Q_{RM}				$1.05 \mu\text{C}$

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

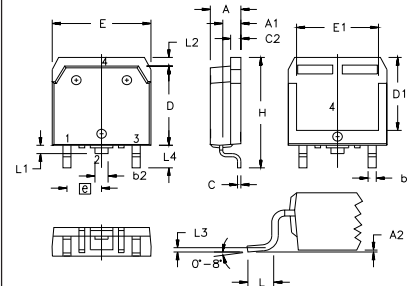
TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010 BSC		0.25 BSC	
L ₄	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

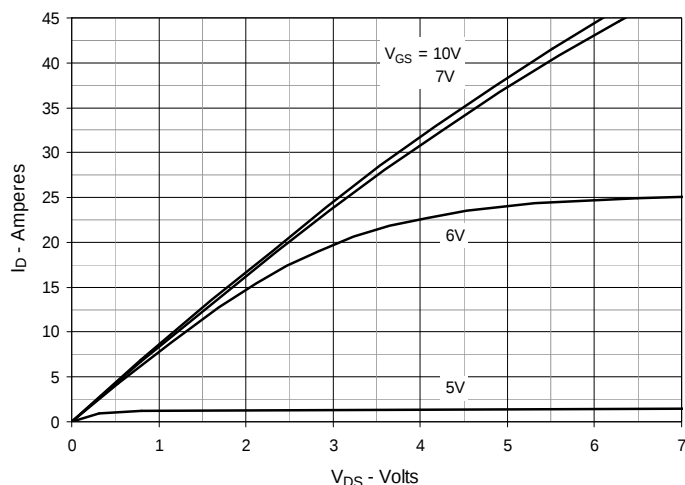


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

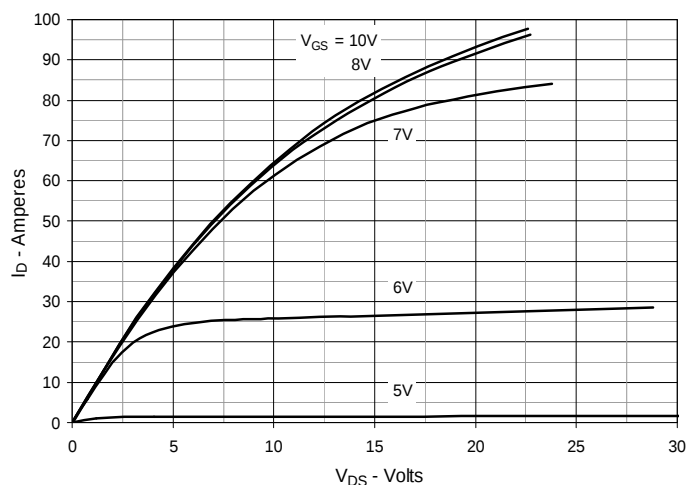


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

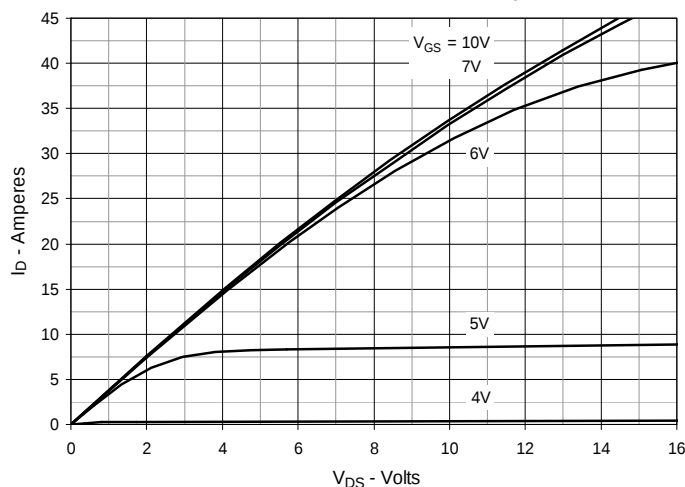


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 21\text{A}$ Value vs. Junction Temperature

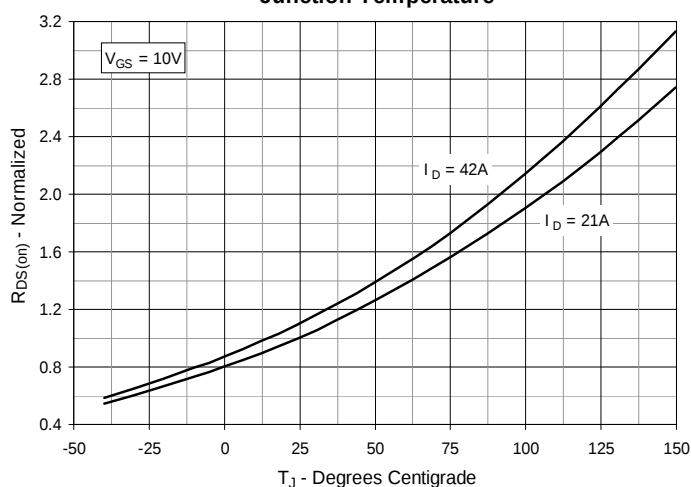


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 21\text{A}$ Value vs. Drain Current

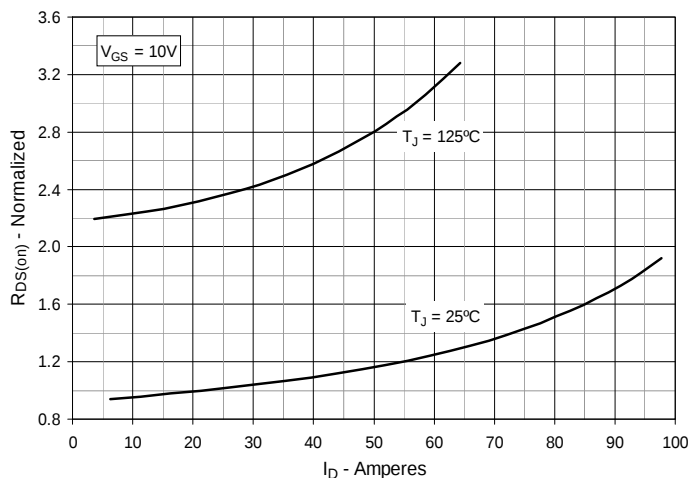


Fig. 6. Maximum Drain Current vs. Case Temperature

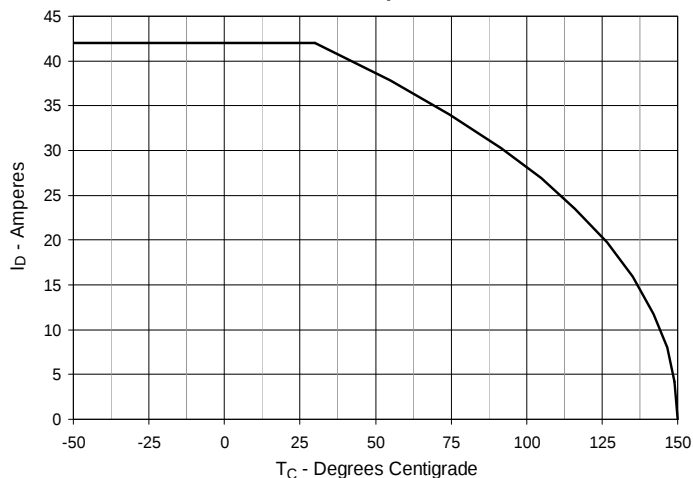


Fig. 7. Input Admittance

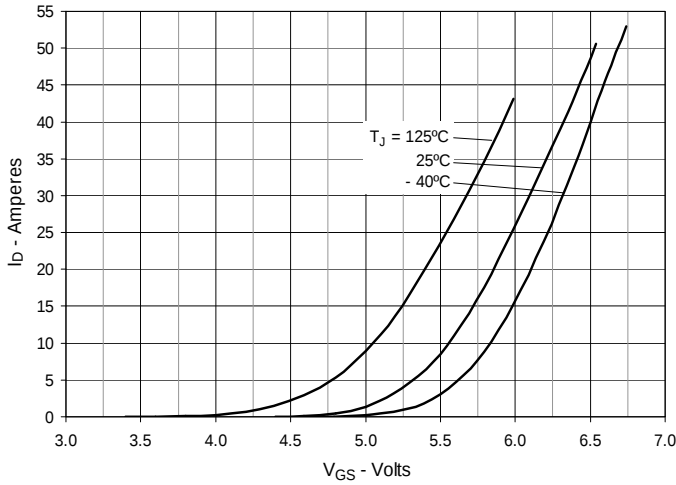


Fig. 8. Transconductance

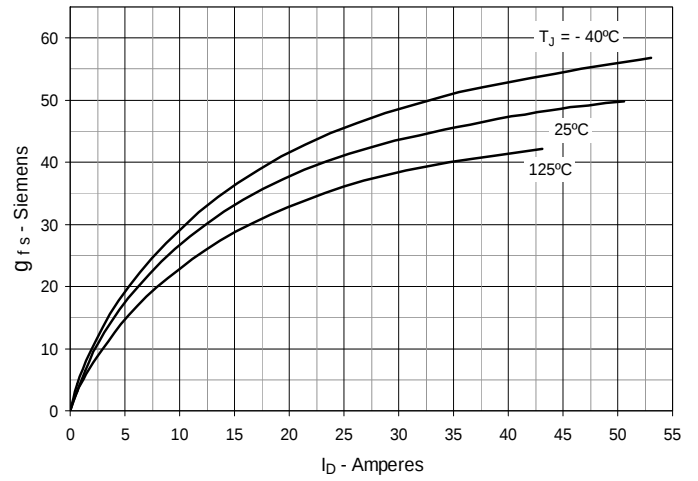


Fig. 9. Forward Voltage Drop of Intrinsic Diode

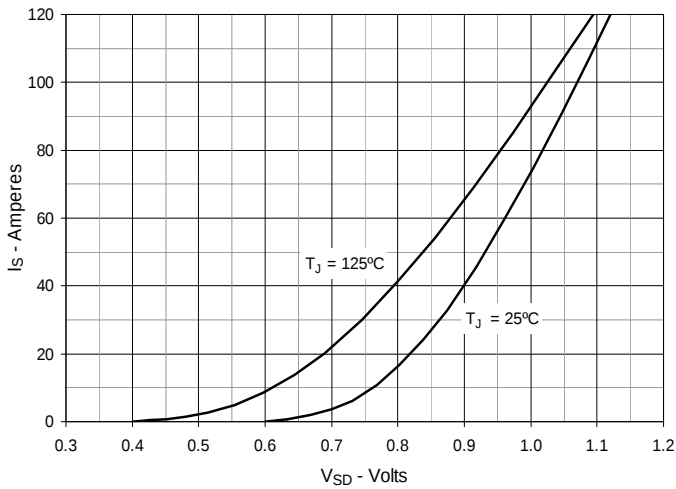


Fig. 10. Gate Charge

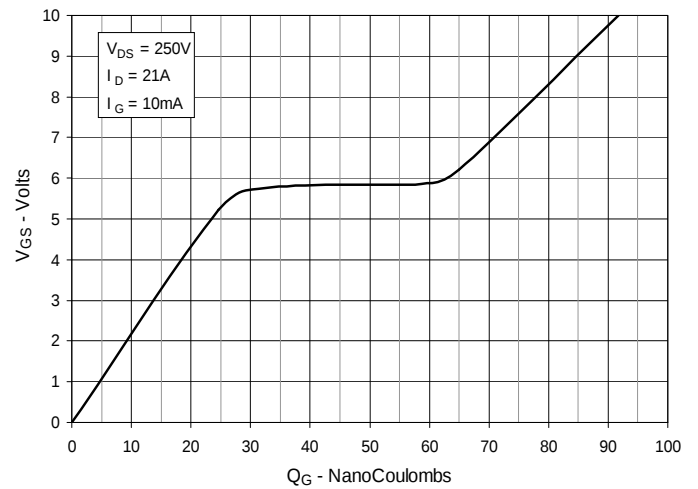


Fig. 11. Capacitance

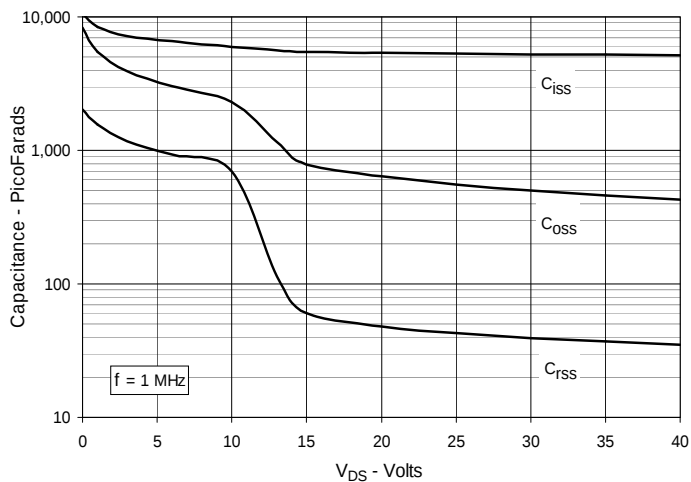


Fig. 12. Maximum Transient Thermal Impedance

